

Optoelectronic Device Wafers

Optoelectronic Device Wafers including Detectors [PIN, avalanche, and metal-semiconductor-metal (MSM) photocathodes, QWIP, and QDOT] and LEDs and Lasers are being used in a number of commercial systems. The most popular system applications include optical data links, night vision, radar, satellite communications, and optical clocking. Wafers with special purpose capability that include edge emitting lasers at 850nm, 980nm, 1004nm, and 14XXnm are available from OSEMI. At **OSEMI**, we have broad experience in the MBE and CBE growth and processing of GaAs and InP based optoelectronic sources and detectors. We would be pleased to put our experience to work for you in the manufacture of wafers in optoelectronics.

Advantages of MBE Grown Optoelectronic Devices:

- excellent wafer uniformity for high device yields
- precise p-n junction location
- stable Carbon-doping to accurate reproducible grading profiles
- precise quantum well thickness and composition
- devices with uniform electrical/optical properties
- integrated optoelectronic devices
- proven device reliability

Excellence in
Compound Semiconductors

GaN CMOS

NetGEN™

Flec-LAB™



Please contact us to discuss how we can assist you with high performance optical device wafer needs.